

TGD N-Channel Enhancement Mode Power MOSFET

Description

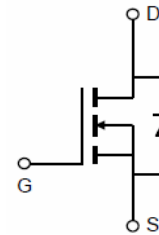
The TGD4012S uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

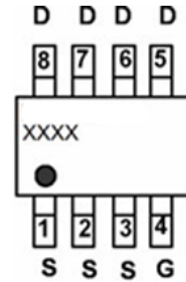
- $V_{DS} = 40V, I_D = 12A$
 $R_{DS(ON)} < 12m\Omega @ V_{GS} = 10V$ (Typ. 8.4 m Ω)
 $R_{DS(ON)} < 18m\Omega @ V_{GS} = 4.5V$ (Typ. 12.3 m Ω)
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

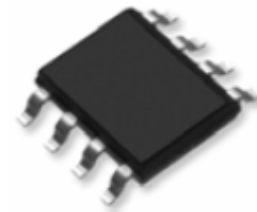
- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



pin Assignment



SOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
TGD4012S	TGD4012S	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	12	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	8.5	A
Pulsed Drain Current	I_{DM}	60	A
Maximum Power Dissipation	P_D	3	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	41.7	$^\circ C/W$
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Electrical Characteristics ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
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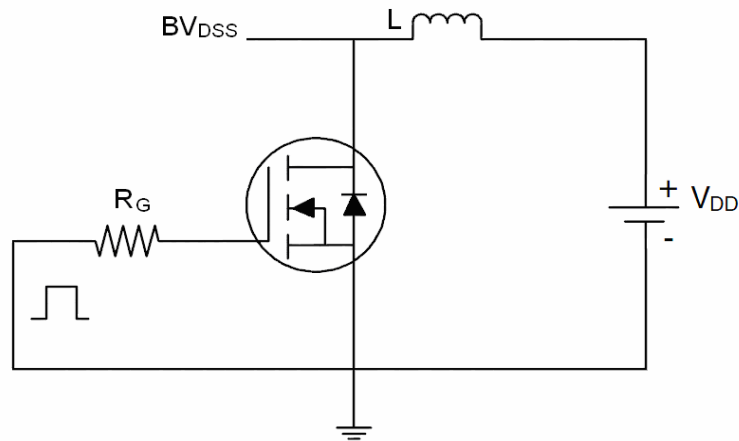
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40	45	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.6	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=10A$	-	8.4	12	m Ω
		$V_{GS}=4.5V, I_D=8A$	-	12.3	18	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=10A$		75	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C_{iss}	$V_{DS}=20V, V_{GS}=0V,$ $F=1.0MHz$	-	1780	-	PF
Output Capacitance	C_{oss}		-	209	-	PF
Reverse Transfer Capacitance	C_{rss}		-	160	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, R_L=2\Omega$ $V_{GS}=10V, R_G=3\Omega$	-	6.4	-	nS
Turn-on Rise Time	t_r		-	17.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	29.6	-	nS
Turn-Off Fall Time	t_f		-	16.8	-	nS
Total Gate Charge	Q_g	$V_{DS}=20V, I_D=10A,$ $V_{GS}=10V$	-	30		nC
Gate-Source Charge	Q_{gs}		-	4.2		nC
Gate-Drain Charge	Q_{gd}		-	9.5		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=10A$	-		1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	12	A
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ C, I_F = 10A$ $di/dt = 100A/\mu s$ ^(Note3)	-	29	-	nS
Reverse Recovery Charge	Q_{rr}		-	26	-	nC

Notes:

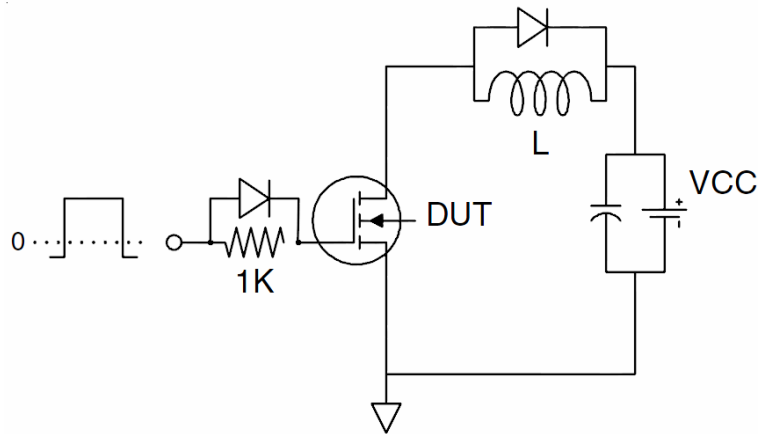
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test circuit

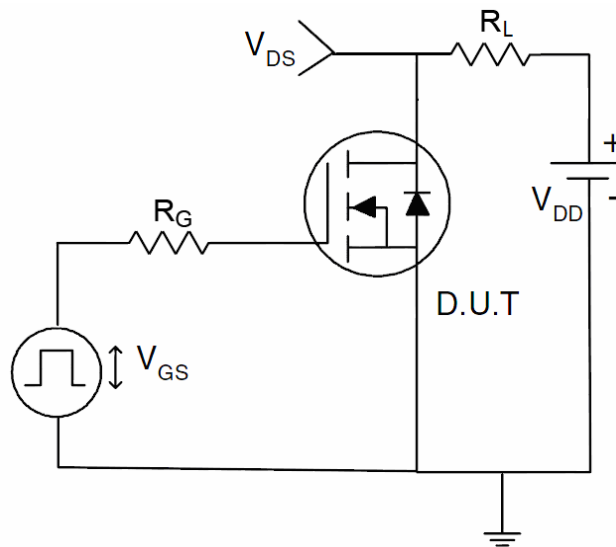
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

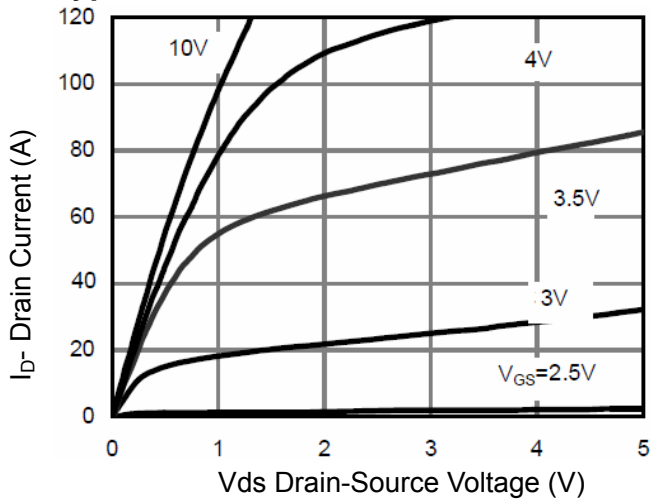


Figure 1 Output Characteristics

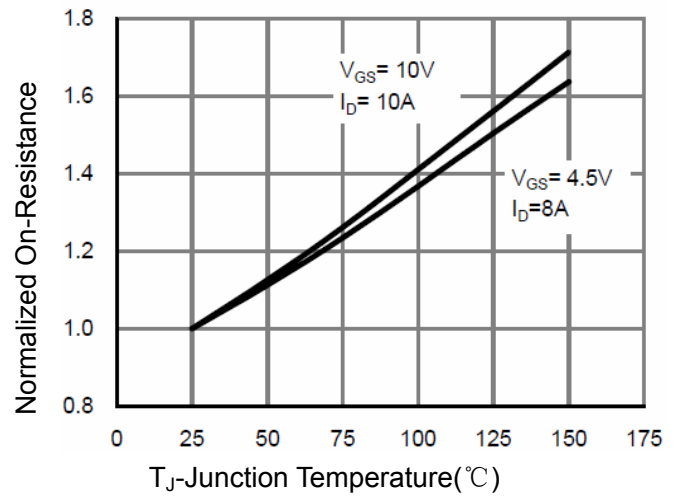


Figure 4 $R_{ds(on)}$ -Junction Temperature

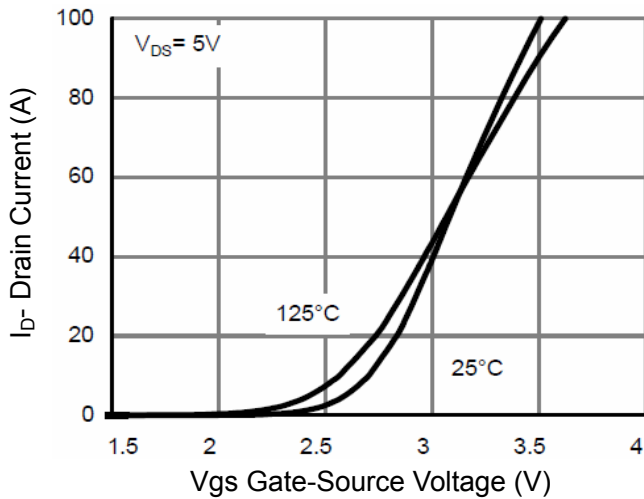


Figure 2 Transfer Characteristics

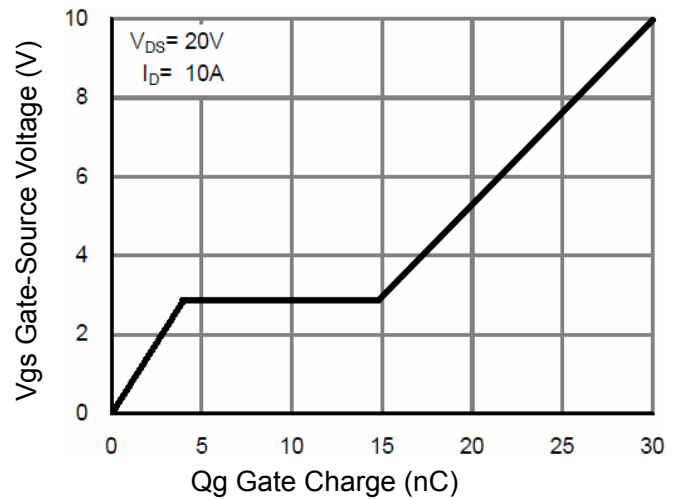


Figure 5 Gate Charge

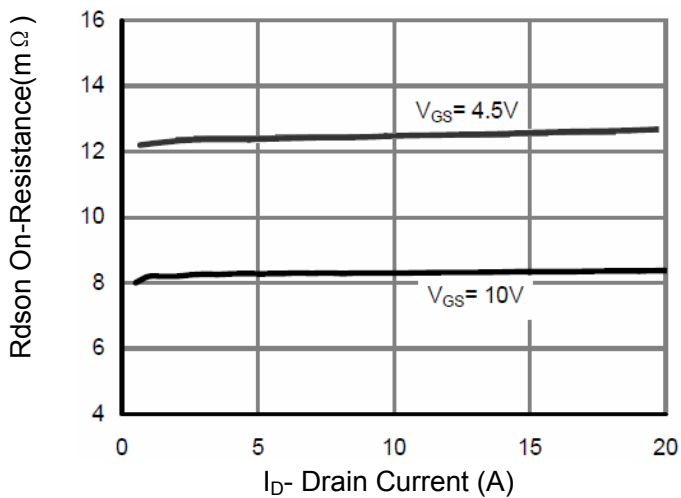


Figure 3 $R_{ds(on)}$ - Drain Current

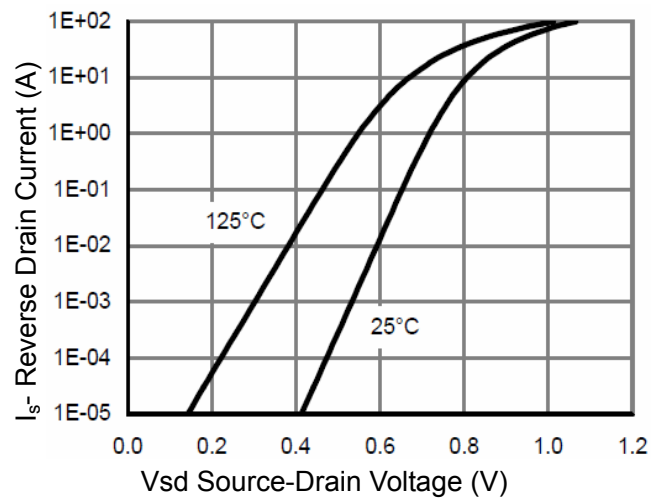


Figure 6 Source- Drain Diode Forward

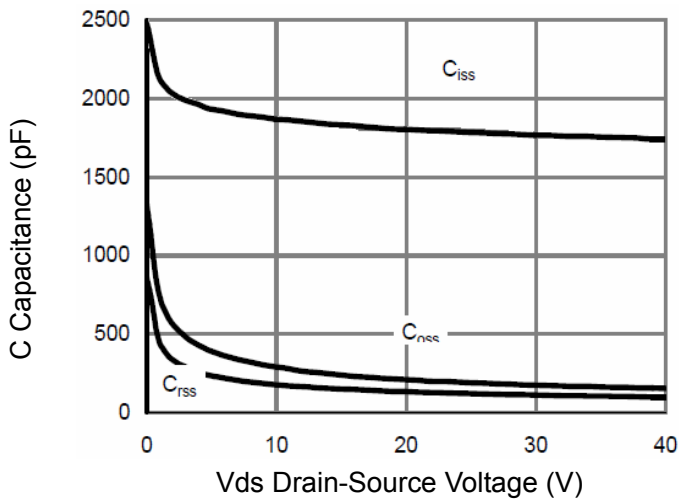


Figure 7 Capacitance vs Vds

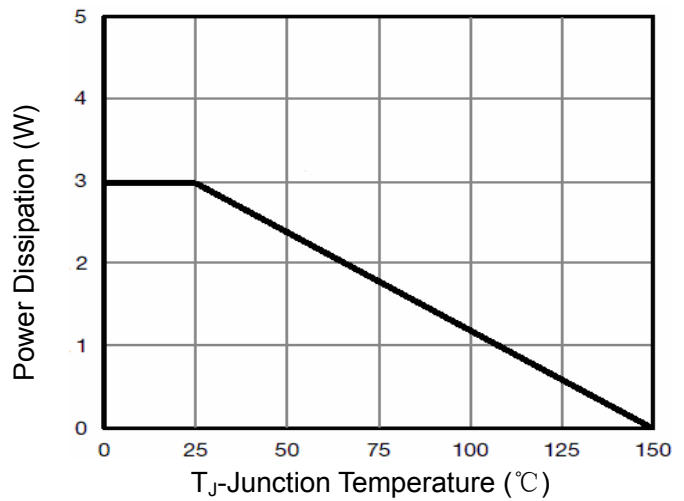


Figure 9 Power De-rating

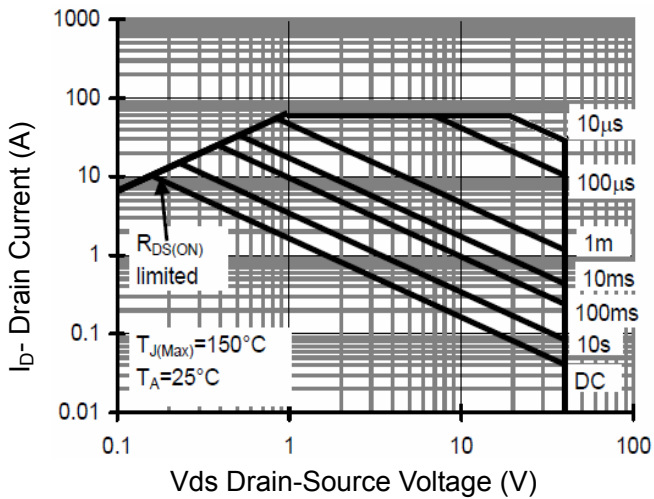


Figure 8 Safe Operation Area

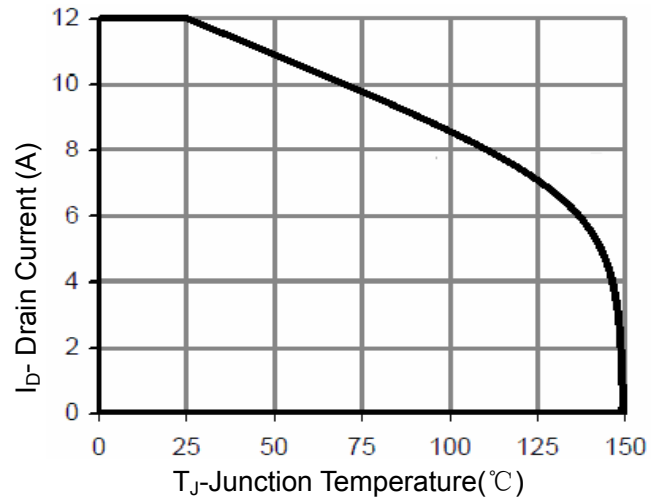


Figure 10 Current De-rating

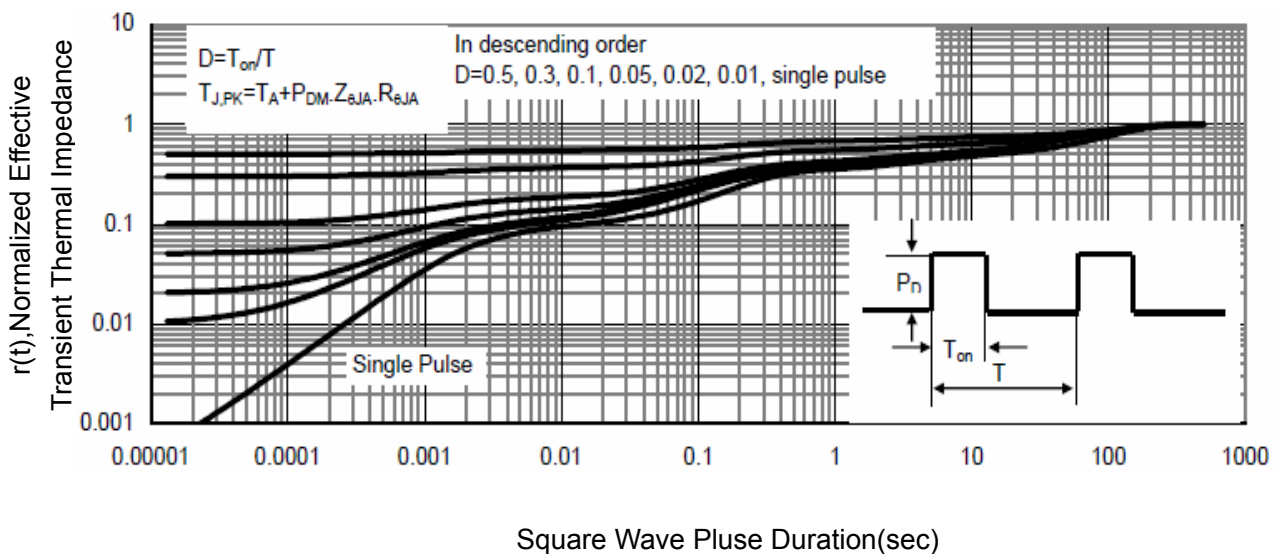
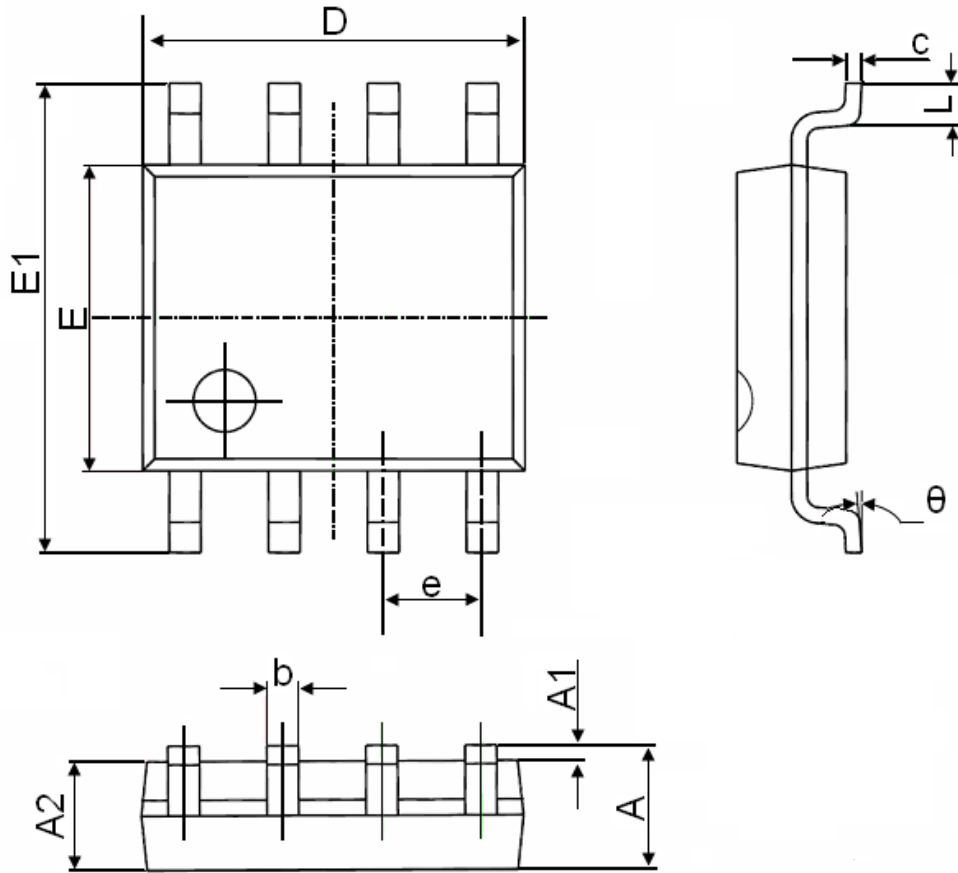


Figure 11 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°